

Docket No.: R2184.0052/P052-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Naoto Jikutani et al.

Application No.: 09/391,472

Group Art Unit: 1765

Filed: September 8, 1999

Examiner: R. Kunemund

For: LASER DIODE HAVING AN ACTIVE  
LAYER CONTAINING N AND OPERABLE  
IN A 0.6 $\mu$ m WAVELENGTH BAND

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached Form PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

The listed documents are not being supplied because they were cited in either one of, or both of, prior Application No. 09/289,955, filed April 13, 1999, now U.S. Patent No. 6,563,851, relied upon in this application for an earlier filing date under 35 U.S.C. § 120, or related Application No. 10/428,074, filed May 2, 2003.

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This Supplemental Information Disclosure Statement is not intended to constitute an admission that any patent, publication or other information referred to herein is "prior art" for this invention unless specifically designated as such. In accordance with 37 C.F.R. § 1.97(g), the filing of this Supplemental Information Disclosure Statement shall not be construed to mean that a search has been made.

Dated: September 4, 2002

Respectfully submitted,

By 

Mark J. Thronson

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Substitute for form 1449A/B/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet

1

of

1

**Complete if Known**

Application Number	09/391,472
Filing Date	September 8, 1999
First Named Inventor	Naoto Jikutani
Art Unit	1765
Prior Examiner Name	R. Kunemund
Attorney Docket Number	R2184.0052/P052-A

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
	AA	4,745,612 A	05/1988	Hayakawa et al.	
	AB	5,383,211 A	01/1995	Van de Walle et al.	
	AC	5,585,649 A	12/1996	Ishikawa et al.	
	AD	6,150,677 A	11/2000	Tanaka et al.	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>5</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				

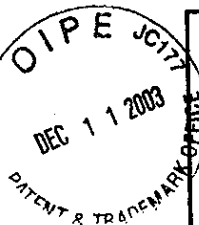
\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	AE	Ougazzaden et al., "Metal Organic Vapor Phase Epitaxy Growth of GAsN on GaAs Using Dimethylhydrazine and Tertiarybutylarsine," Applied Physics Letters, Vol. 70, No. 21, May 26, 1997, pp. 2861-2863	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.



Inventor: Naoto Jikutani et al.

Atty Docket No.: R2184.0052/P052-A

Application No.: 09/391,472

Filing Date: September 8, 1999

Title: LASER DIODE HAVING AN ACTIVE LAYER ...

**Documents Filed:**

RCE Transmittal  
Amendment  
Supplemental IDS w/Form PTO/SB/08  
Petition for Extension of Time  
Form PTO-2038

Via: PTO Run  
Sender's Initials: MJT/ml



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AL 9-5-03